



PNP POWER TRANSISTORS

COMPLEMENTARY TO THE TIP29 SERIES

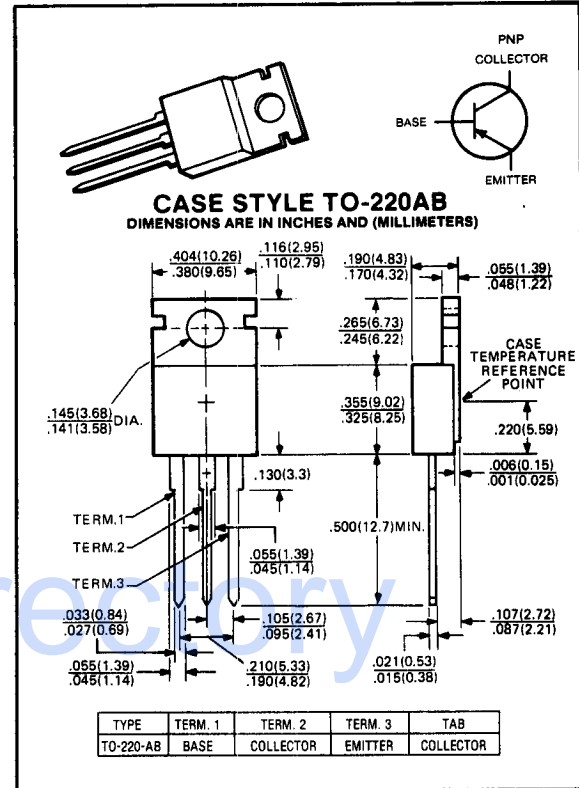
TIP 30 Series

-40 ~ -100 VOLTS
-1 AMP, 30 WATTS

The TIP30 Series power transistors are designed for use in general purpose amplifier and switching applications.

Features:

- Designed for complementary use with TIP29 series
- 30W at 25°C case temperature
- -1A continuous collector current
- -3A peak collector current
- Minimum f_T of 3 MHz at 10V, 0.02A
- Customer-specified selections available
- Designed for power amplifier and high-speed switching applications



Datasheet.Directory

maximum ratings ($T_C = 25^\circ C$) (unless otherwise noted)

RATING	SYMBOL	TIP30	TIP30A	TIP30B	TIP30C	UNITS
Collector-Emitter Voltage	V_{CEO}	-40	-60	-80	-100	Volts
Collector-Base Voltage	V_{CBO}	-80	-100	-120	-140	Volts
Emitter Base Voltage	V_{EBO}	-5	-5	-5	-5	Volts
Collector Current — Continuous	I_C	-1	-1	-1	-1	A
Peak	I_{CM}	-3	-3	-3	-3	A
Base Current — Continuous	I_B	-0.4	-0.4	-0.4	-0.4	A
Total Power Dissipation @ $T_A = 25^\circ C$ @ $T_C = 25^\circ C$	P_D	2 30	2 30	2 30	2 30	Watts
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-65 to +150	-65 to +150	-65 to +150	-65 to +150	$^\circ C$

thermal characteristics

Thermal Resistance, Junction to Case	$R_{\theta JC}$	4.17	4.17	4.17	4.17	$^\circ C/W$
Maximum Lead Temperature for Soldering Purposes: $\frac{1}{8}$ " from Case for 5 Seconds	T_L	250	250	250	250	$^\circ C$

electrical characteristics ($T_C = 25^\circ C$) (unless otherwise specified)

CHARACTERISTIC	SYMBOL	MIN	TYP	MAX	UNIT
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off characteristics

Collector-Emitter Breakdown Voltage ($I_C = -30mA$)	TIP30 TIP30A TIP30B TIP30C	V_{CEO}	-40 -60 -80 -100	— — — —	— — — —	Volts
Collector Cutoff Current ($V_{CE} = -30V$) ($V_{CE} = -60V$)	TIP30, TIP30A TIP30B, TIP30C	I_{CEO}	— —	— —	-0.3 -0.3	mA
Collector Cutoff Current ($V_{CE} = -80V$) ($V_{CE} = -100V$) ($V_{CE} = -120V$) ($V_{CE} = -140V$)	TIP30 TIP30A TIP30B TIP30C	I_{CES}	— — — —	— — — —	-0.2 -0.2 -0.2 -0.2	mA
Emitter Cutoff Current ($V_{EB} = -5V, I_C = 0$)		I_{EBO}	—	—	-1	mA

second breakdown

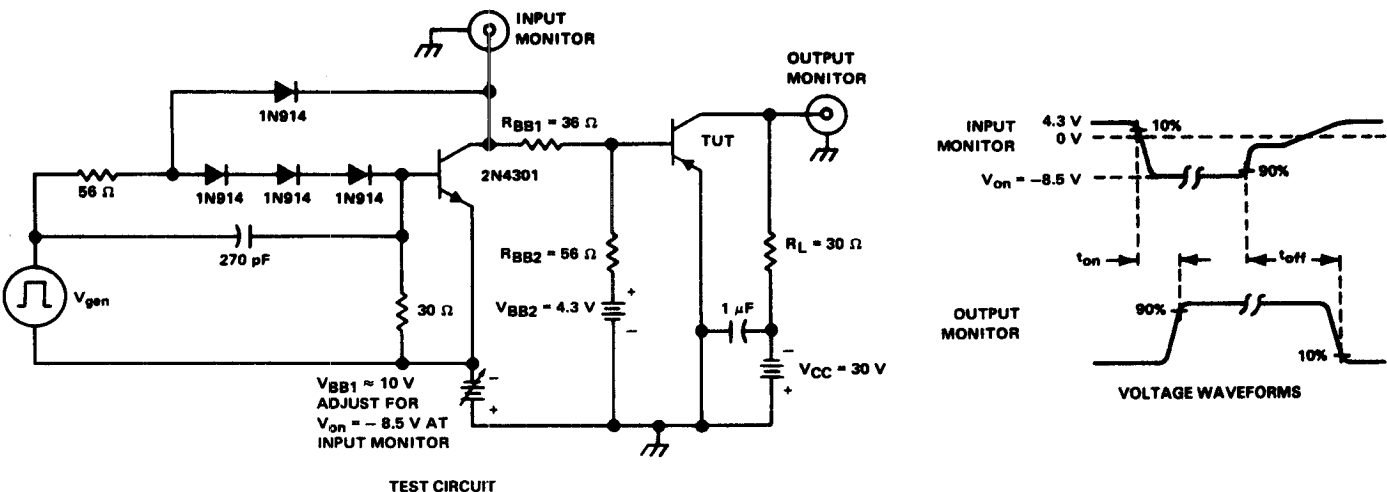
Second Breakdown with Base Forward Biased	FBSOA	SEE FIGURE 3
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on characteristics

DC Current Gain ($I_C = -0.2A, V_{CE} = -4V$) ($I_C = 1A, V_{CE} = 4V$)	h_{FE}	20 15	— —	— 75	—
Collector-Emitter Saturation Voltage ($I_C = -1A, I_B = -125mA$)	$V_{CE(sat)}$	—	—	-0.7	V
Base-Emitter Voltage ($I_C = -1A, V_{CE} = -4V$)	$V_{BE(on)}$	—	—	-1.3	V

switching characteristics

Turn-on Time	$R_L = 30\Omega, I_C = -1A$ $I_{B1} = I_{B2} = 0.1A$ $V_{BE(off)} = 4.3V$	t_{on}	—	0.3	—	μS
Turn-off Time		t_{off}	—	1	—	



- NOTES:
- V_{gen} is a 30-V pulse into a 50 Ω termination.
 - The V_{gen} waveform is supplied by the following characteristics: $t_r \leq 15$ ns, $t_f \leq 15$ ns, $Z_{out} = 50 \Omega$, $t_w = 20 \mu s$, duty cycle $\leq 2\%$.
 - Waveforms are monitored on an oscilloscope with the following characteristics: $t_r \leq 15$ ns, $R_{in} \geq 10$ M Ω , $C_{in} \leq 11.5$ pF.
 - Resistors must be noninductive types.
 - The d-c power supplies may require additional bypassing in order to minimize ringing.

FIGURE 1. RESISTIVE-LOAD SWITCHING

STATIC FORWARD CURRENT TRANSFER RATIO
vs
COLLECTOR CURRENT

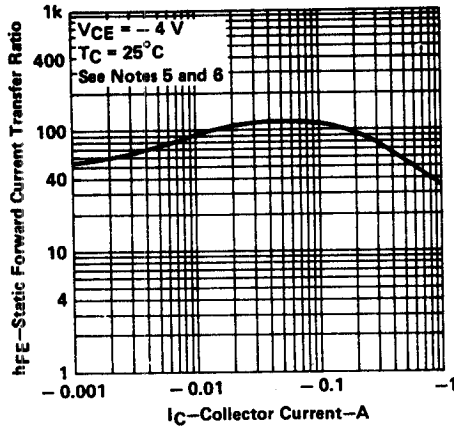


FIGURE 2. TYPICAL CHARACTERISTICS

- NOTES: 5. These parameters must be measured using pulse techniques, $t_w = 300 \mu s$, duty cycle $\leq 2\%$.
6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

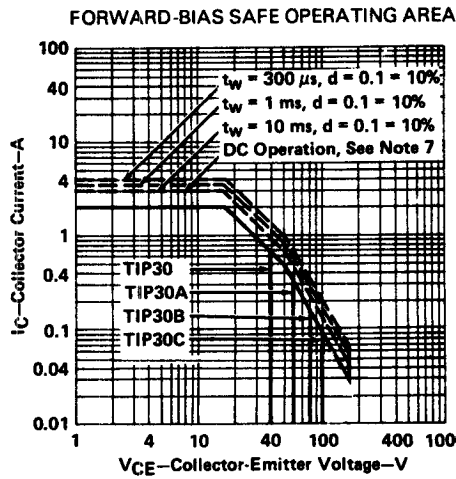


FIGURE 3. MAXIMUM SAFE OPERATING AREA

- NOTE 7: This combination of maximum voltage and current values may be achieved only when switching from saturation to cutoff with a clamped inductive load.

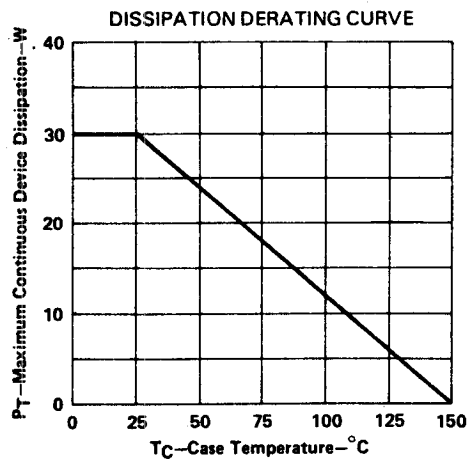


FIGURE 4. THERMAL INFORMATION